

Copper Sputtering Target (4N-5N Purity)

This copper sputtering target is available in purities ranging from 4N to 5N. It is produced using melting technology and applied in semiconductor, decorative coating, and advanced packing fields.



Product Overview

High-Purity Copper Sputtering Targets

These high-purity copper sputtering targets are engineered for advanced thin-film deposition in semiconductor, decorative coating, and touch screen manufacturing. By employing advanced melting technology and controlled microstructure deformation, these targets provide superior electrical and thermal conductivity while minimizing particle formation during the PVD process. Available in both planar and rotary configurations to meet diverse industrial requirements.

Technical Specifications

Available Forms

- Planar Target (up to G8.5 generation)
- Rotary Target

Purity Levels	99.9%, 99.99% (4N), 99.999% (5N), 99.9999% (6N)
Oxygen Content	< 1 ppm

Performance Features

Key Performance Indicators

29

Atomic Number

1 ppm

Max Oxygen Content

Analytical Methods

Component	Method
Metallic Elements	GDMS and ICP-OES
Gas Elements	LECO